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**RESPONSE UNDER 37 C.F.R. § 1.116
EXPEDITED PROCEDURE REQUESTED
EXAMINING GROUP 2822**

PATENT
Customer No. 22,852
Attorney Docket No. 06484.0073

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Shi-Tron LIN

Serial No.: 09/740,017

Filed: December 20, 2000

For: TRANSISTOR STRUCTURE FOR
ELECTROSTATIC DISCHARGE
PROTECTION CIRCUIT

Group Art Unit: 2822

Examiner: S. Meier

Mail Stop AF

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

AMENDMENT AFTER FINAL

In reply to the Final Office Action of April 29, 2003, and pursuant to 37 C.F.R.

§ 1.116, Applicant proposes that this application be amended as follows:

IN THE CLAIMS:

Please cancel claim 103 without prejudice or disclaimer of the subject matter thereof, and amend claims 1, 101, and 102, and add new claim 104 as follows:

1. (Amended) An electrostatic discharge (ESD) protection device, comprising:

a semiconductor layer;

a first diffusion region formed in the layer;

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